

HCS05FH120E1R1

1200V/5.5mΩ Half Bridge SiC MOSFET Module

Description

The HCS05FH120E1R1 is a half bridge sic MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Solar Inverter Systems, Fuelcell-DC/DC converter, Uninterruptible Power Supplier, Energy Storage Systems.



Features

- Blocking voltage:1200V
- 5.5mΩ Rds(on)
- Low Switching Losses
- 175°C maximum junction temperature
- Si3N4 AMB
- Thermistor inside

Applications

- Solar inverter Systems
- Fuel cell-DC/DC converter
- Uninterruptible Power Supplier
- Energy Storage Systems

Circuit diagram

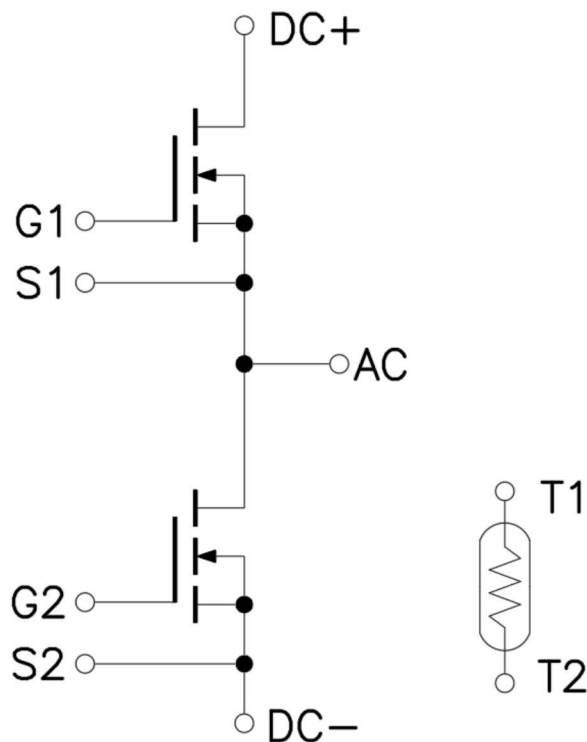


Figure 1 Out drawing & circuit diagram for HCS05FH120E1R1

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Pin Configuration and Marking Information

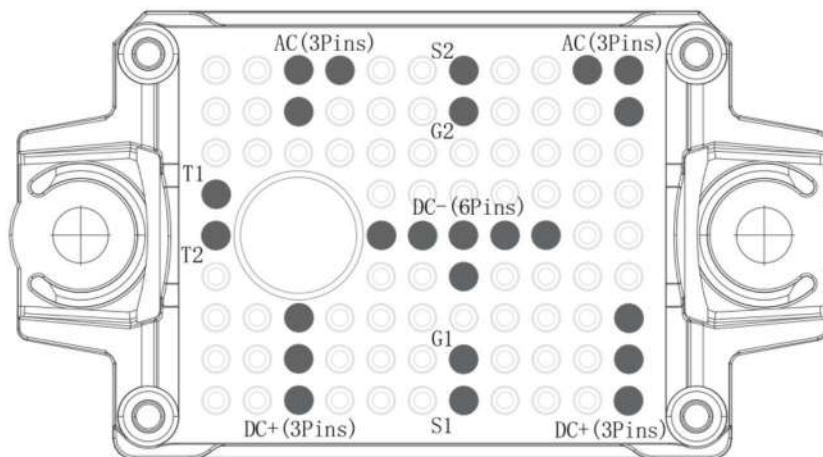


Figure 2. Pin configuration

Symbol	Description
AC	Output terminal of half bridge
S2	Low side source signal terminal
G2	Low side gate signal terminal
DC+	DC+ Bus connection
DC-	DC- Bus connection
S1	High side source signal terminal
G1	High side gate signal terminal
T1	Thermistor connection 1
T2	Thermistor connection 2

Module

Parameter	Conditions	Value	Unit
Isolation voltage	RMS, f=50Hz, t =1min	3.4	kV
Clearance	Terminal to Terminal	5	mm
	Terminal to Heatsink	10	mm
Creepage distance	Terminal to Terminal	6.3	mm
	Terminal to Heatsink	12.7	mm
Comparative Tracking Index	-	600	-
Weight	-	26	g

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Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short	1200	V
V _{GSS}	Gate-Source Voltage(+)	D-S Short	21	V
V _{GSS}	Gate-Source Voltage(-)	D-S Short	-2	V
V _{GSSSurge}	G-S Voltage(t _{surge} <300nsec)	D-S Short, Note1	-6 to 23	V
I _{DS}	DC Continuous Drain Current	T _r =95°C, Note2	150	A
I _{SD}	Source (Body diode) Current	T _r =95°C, with ON signal	150	A
I _{DP}	Drain Pulse Current, Peak	Less than 1ms, Note3	400	A
T _j	junction temperature	-	-40 to 175	°C
T _{stg}	Storage temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, +18V/0V.

Note2: Case temperature(T_c) is defined on the surface of base plate just under the chips.

Note3: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _c =25°C	-	5	-	kΩ
ΔR/R	Deviation of R ₁₀₀	T _c =100°C, R ₁₀₀ =493Ω	5	-	5	%
P ₂₅	Power dissipation	T _c =25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ =R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ =R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

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MOSFET Electrical characteristics $T_j=25^{\circ}\text{C}$ unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA		1200	-	-	V
I _{DSS}	Zero gate voltage drain current	V _{DS} =1200V, V _{GS} =0V		-	-	160	μA
V _{GS(th)}	Gate-source threshold voltage	I _D =73mA, V _{DS} =V _{GS}		2.8	-	4.8	V
I _{GSS+}	Gate-Source Leakage Current	V _{GS} =21V, V _{DS} =0V, T _j =25°C		-	-	200	nA
I _{GSS-}		V _{GS} =-2V, V _{DS} =0V, T _j =25°C		-200	-	-	nA
R _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =150A	T _j =25°C	-	5.5	6.9	mΩ
		V _{GS} =+18V	T _j =175°C	-	13	-	mΩ
V _{DS(on)} (Chip)	Static drain-source On-state voltage	I _D =150A	T _j =25°C	-	0.83	1.04	V
		V _{GS} =+18V	T _j =175°C	-	1.95	-	V
C _{iss}	Input capacitance	V _D =10V, V _{GS} =0V, f =200kHz		-	14.5	-	nF
C _{oss}	Output capacitance			-	0.4	-	nF
C _{rss}	Reverse transfer capacitance			-	0.03	-	nF
Q _G	Total gate charge	V _{DD} =600V, I _D =150A, V _{GS} =+15/0V		-	520	-	nC
R _{Gint}	Internal Gate Resistance	T _j =25°C		-	1.9	-	Ω
t _{d(on)}	Turn-on delay time	V _{DD} =600V I _D =150A V _{GS} =+18/0V R _G =3.3Ω Inductive load switching operation	T _j =25°C	-	58	-	ns
			T _j =150°C	-	55	-	
t _r	Rise time		T _j =25°C	-	27	-	ns
			T _j =150°C	-	18	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	245	-	ns
			T _j =150°C	-	290	-	
t _f	Fall time		T _j =25°C	-	40	-	ns
			T _j =150°C	-	43	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	3.54	-	mJ
			T _j =150°C	-	3.35	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	1.59	-	mJ
			T _j =150°C	-	1.76	-	
R _{th(j-c)}	FET Thermal Resistance	Junction to Case/MOSFET		-	0.12	-	K/W
R _{th(c-f)}	Contact thermal resistance	With thermal conductive grease/MOSFET		-	0.15	-	K/W

Assumes Thermal Conductivity of grease is 2.8 W/m·K and thickness is 50um.

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Body Diode Electrical characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified, chip: Target)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{SD}	Body Diode Forward Voltage	V _{GS} =0V I _{SD} =150A	T _j =25°C	-	3.3	-	V
			T _j =150°C	-	4.0	-	
T _{rr}	Reverse recovery time	V _{DD} =600V I _D =150A	T _j =25°C	-	41.5	-	ns
			T _j =150°C	-	45	-	
Q _{rr}	Reverse recovery charge	V _{GS} =+18/0V R _G =3.3Ω	T _j =25°C	-	2.19	-	μC
			T _j =150°C	-	3.94	-	
E _{rr}	Diode switching power dissipation	Inductive load switching operation	T _j =25°C	-	0.64	-	mJ
			T _j =150°C	-	1.42	-	

Test Conditions

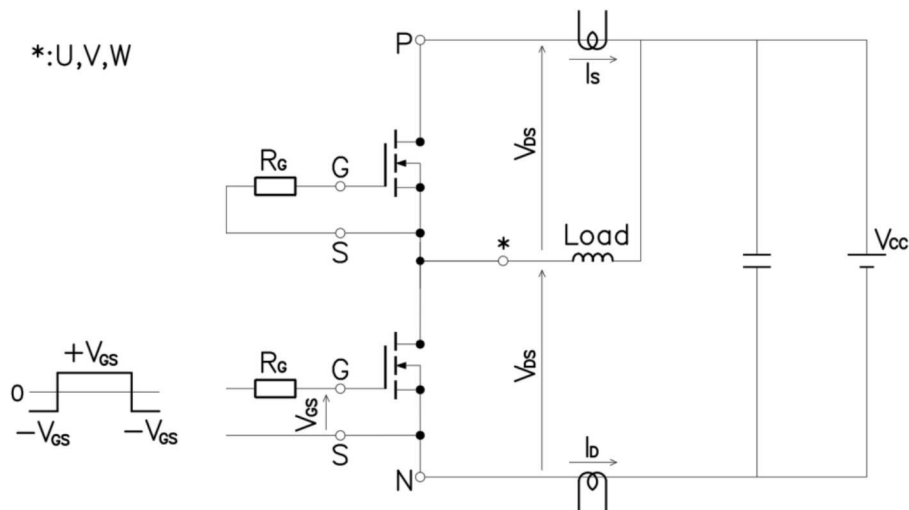


Figure 3. Switching time measure circuit

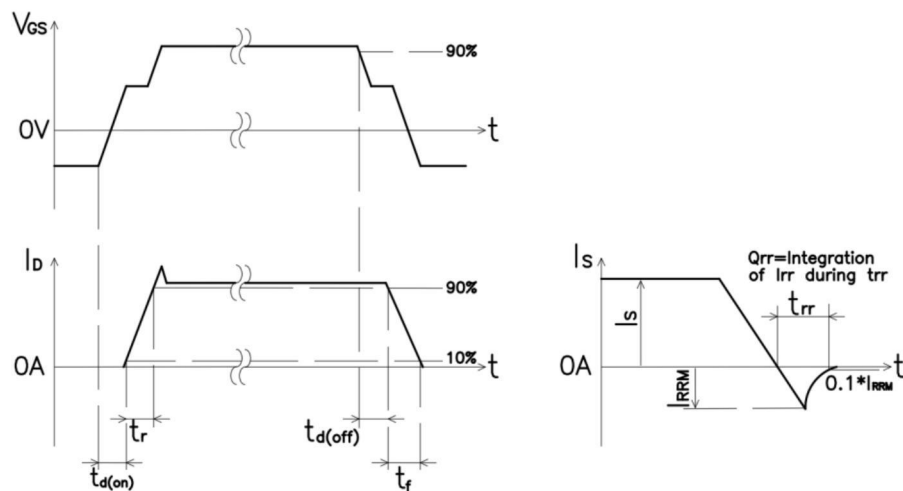


Figure 4. Switching time definition

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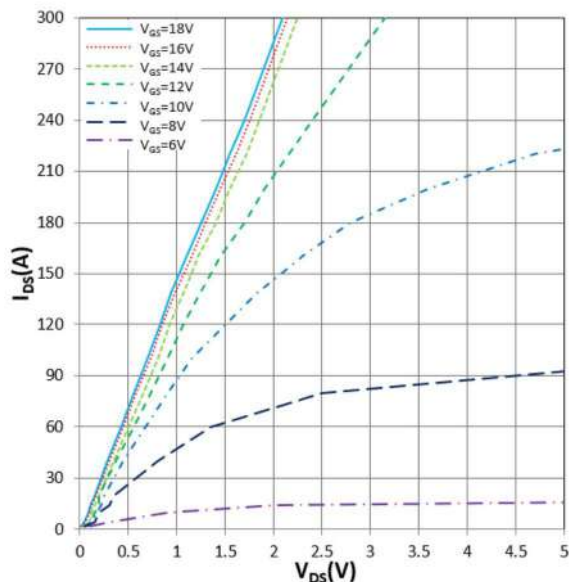


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

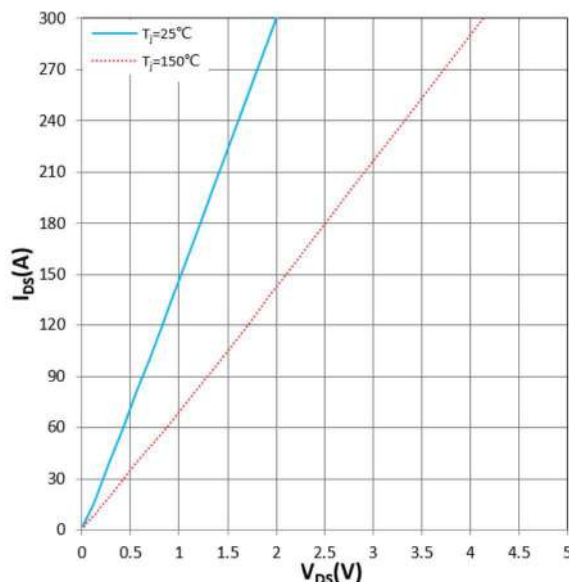


Figure 6. I_{DS} vs V_{DS}
 $V_{GS} = +18\text{V}$

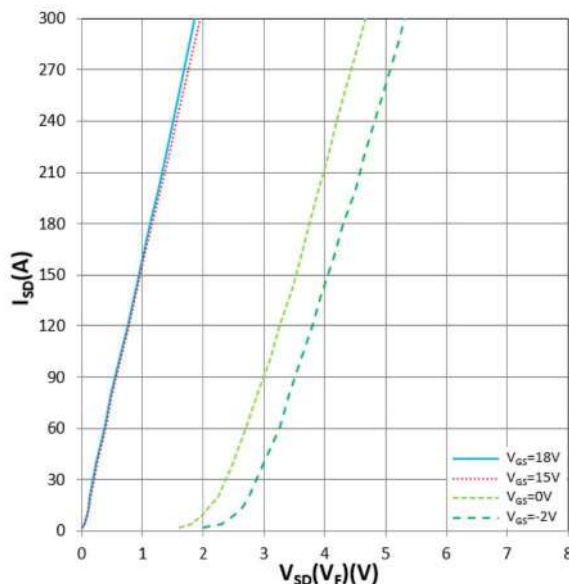


Figure 7. I_{SD} vs $V_{SD}(V_F)$
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

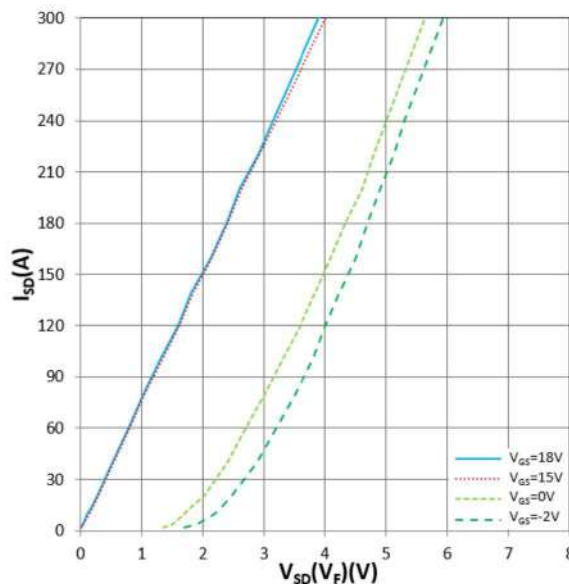


Figure 8. I_{SD} vs $V_{SD}(V_F)$
 $T_j = 150^\circ\text{C}$, V_{GS} parameter

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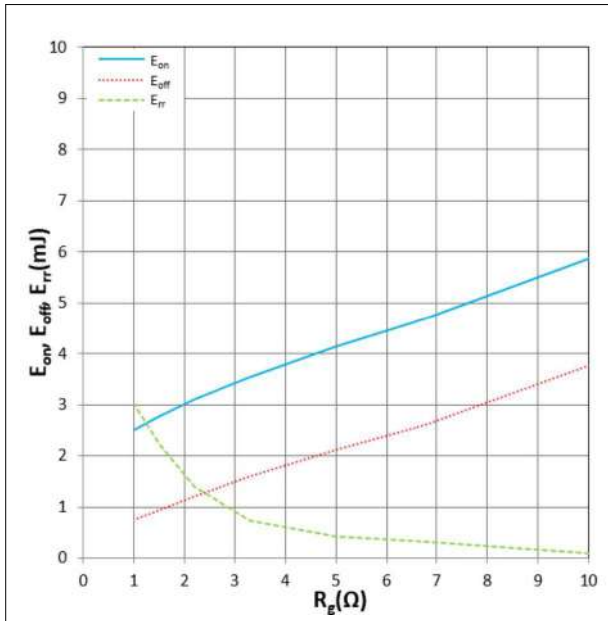


Figure 9. E_{on} , E_{off} , E_{rr} vs R_G
 $T_j=25^{\circ}\text{C}$, $I_D=150\text{A}$, $V_{GS}=+18\text{V}/0\text{V}$

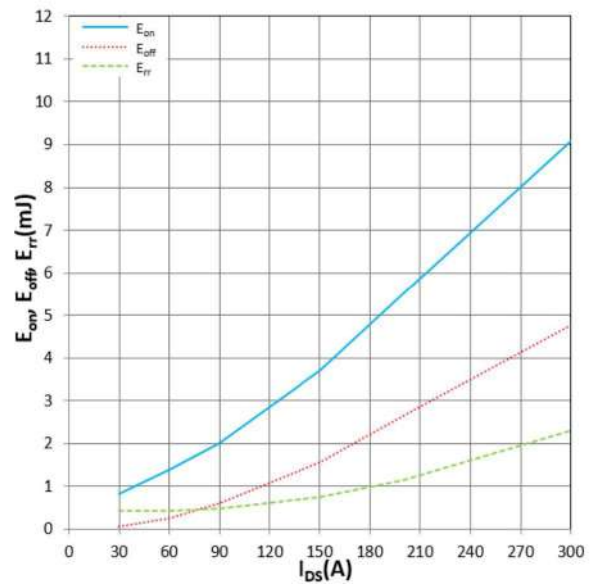


Figure 10. E_{on} , E_{off} , E_{rr} vs I_{DS}
 $T_j=25^{\circ}\text{C}$, $R_G=3.3\Omega$, $V_{GS}=+18\text{V}/0\text{V}$

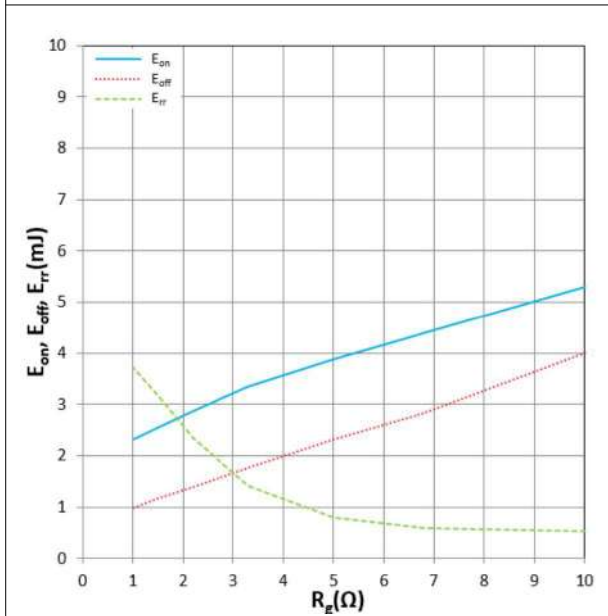


Figure 11. E_{on} , E_{off} , E_{rr} vs R_G
 $T_j=150^{\circ}\text{C}$, $I_D=150\text{A}$, $V_{GS}=+18\text{V}/0\text{V}$

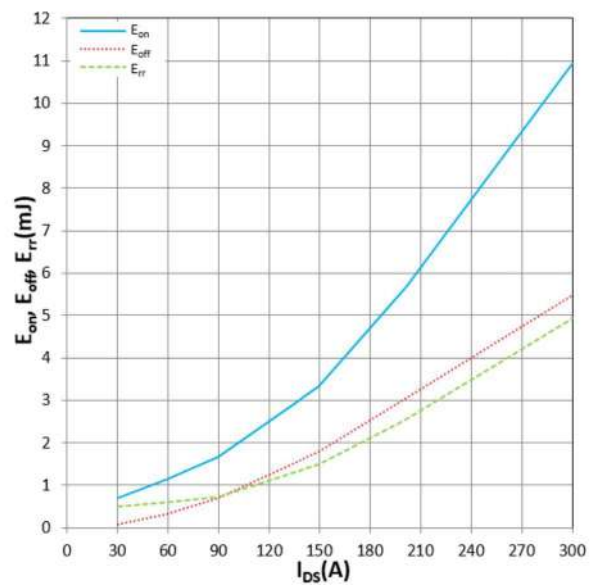
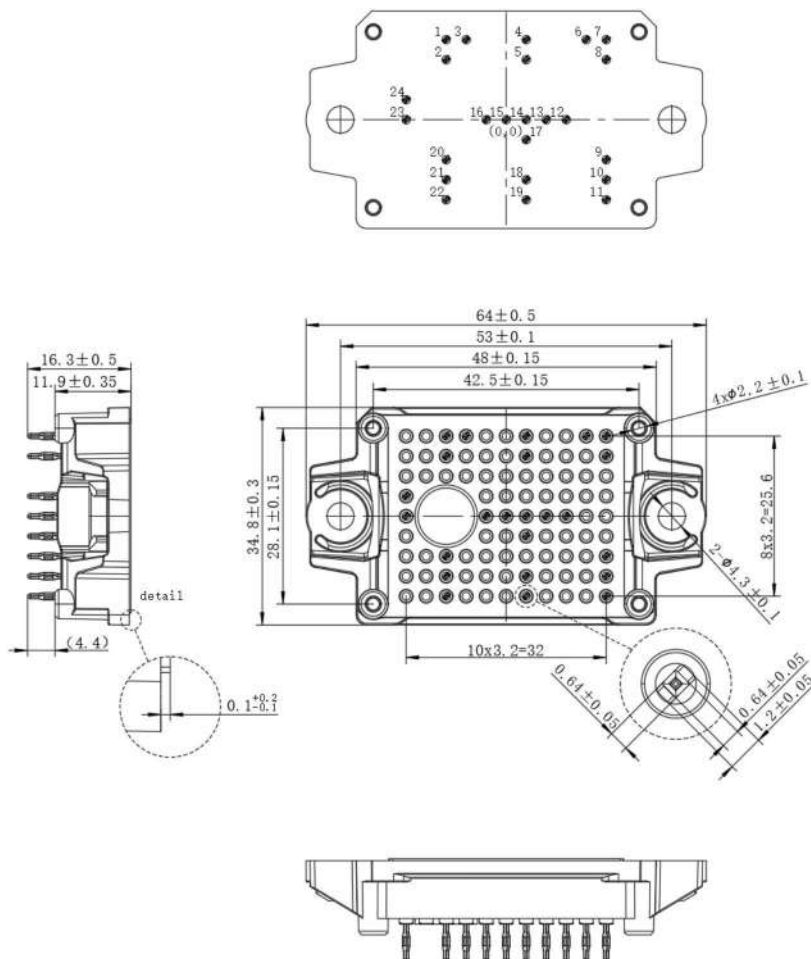


Figure 12. E_{on} , E_{off} , E_{rr} vs I_{DS}
 $T_j=150^{\circ}\text{C}$, $R_G=3.3\Omega$, $V_{GS}=+18\text{V}/0\text{V}$

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Package dimensions



Pin table		
Pin	X	Y
1	-9.6	12.8
2	-9.6	9.6
3	-6.4	12.8
4	3.2	12.8
5	3.2	9.6
6	12.8	12.8
7	16	12.8
8	16	9.6
9	16	-6.4
10	16	-9.6
11	16	-12.8
12	9.6	0
13	6.4	0
14	3.2	0
15	0	0
16	-3.2	0
17	3.2	-3.2
18	3.2	-9.6
19	3.2	-12.8
20	-9.6	-6.4
21	-9.6	-9.6
22	-9.6	-12.8
23	-16	0
24	-16	3.2

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Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

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Revision History

Document Version	Description of Changes
RevX.0.1	Released

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